

Silicon PNP Power Transistors

2SA770 2SA771

DESCRIPTION

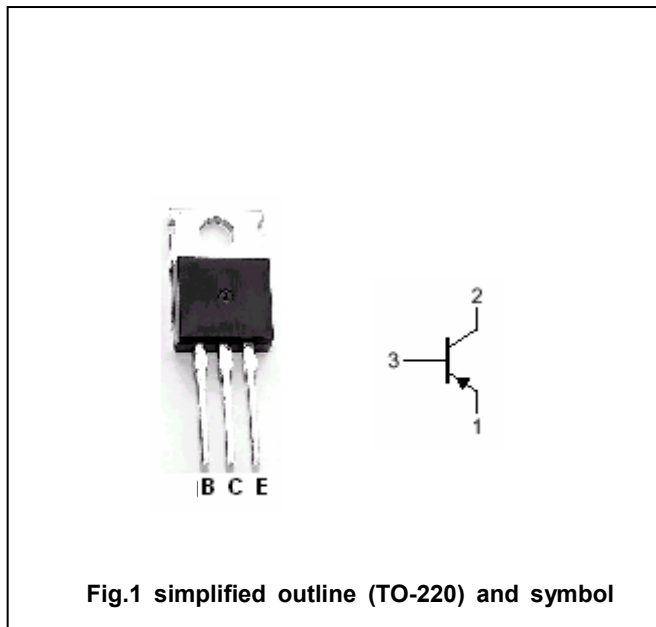
- With TO-220 package
- Complement to type 2SC1985/1986
- Low collector saturation voltage

APPLICATIONS

- For general and industrial purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SA770	-60	V
		2SA771	-80	
V _{CEO}	Collector-emitter voltage	2SA770	-60	V
		2SA771	-80	
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-6	A
I _B	Base current		-3	A
P _C	Collector power dissipation	T _C =25°C	40	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA770	I _C =-25mA, I _B =0	-60		V
		2SA771		-80		
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-1.0	V
I _{CBO}	Collector cut-off current	2SA770	V _{CB} =-60V; I _E =0		-1.0	mA
		2SA771		V _{CB} =-80V; I _E =0		
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-1.0	mA
h _{FE}	DC current gain	I _C =-1A; V _{CE} =-4V	40			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-12V		10		MHz

Switching times

t _r	Rise time	I _C =-3A; V _{CC} =-9V I _{B1} =-I _{B2} =-0.4A; R _L =3Ω		0.9		μs
t _{stg}	Storage time			1.0		μs
t _f	Fall time			0.1		μs

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)